



《风光欣》技术资料

S 9015

PNP EPITAXIAL SILICON TRANSISTOR

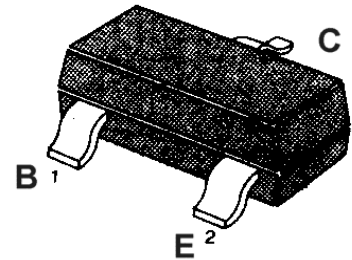
LOW FREQUENC.LOW NOISE AMPLIFIER

Complement to S9014

ABSOLUTE MAXIMUM RATINGS(TA=25)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter -Base Voltage	V _{EBO}	-5	V
Collector Current	I _c	-100	mA
Collector Dissipation	P _c	225	mW
Junction Temperature	T _J	150	
Storage Temperature	T _{STG}	-55 ~150	

SOT-23



ELECTRCAL CHARACTERISTICS(TA=25)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV _{CB0}	I _c = -100 μ A, I _E =0	-50			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _c = -1mA, I _B =0	-45			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = -100 μ A, I _c =0	-5			V
Collector Cut-off Current	I _{CB0}	V _{CB} = -50V, I _E =0			-50	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = -5V, I _c =0			-50	nA
DC Current Gain	h _{FE}	V _{CE} = -5V, I _c = -1mA	60	200	600	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c = -100mA, I _B = -5mA		-0.2	-0.7	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _c = -100mA, I _B = -5mA		-0.82	-1.0	V
Base-Emitter On Voltage	V _{BE(on)}	V _{CE} = -5V, I _c = -2mA	-0.6	-0.65	-0.75	V
Output Capacitance	C _{OB}	V _{CB} = -10V, I _E =0, F=1MHZ		4.5	7.0	pF
Curent Gain-Bandwidth Product	f _T	V _{CE} = -5V, I _c = -10mA	100	190		MHz
Noise Figure	NF	V _{CE} = -5V, I _c = -0.2mA f=1KHz, R _s =1K		0.70	10.0	dB

Hfe CLASSIFICATION

Classification	A	B	C
H _{FE} (1)	60~150	100~300	200~600